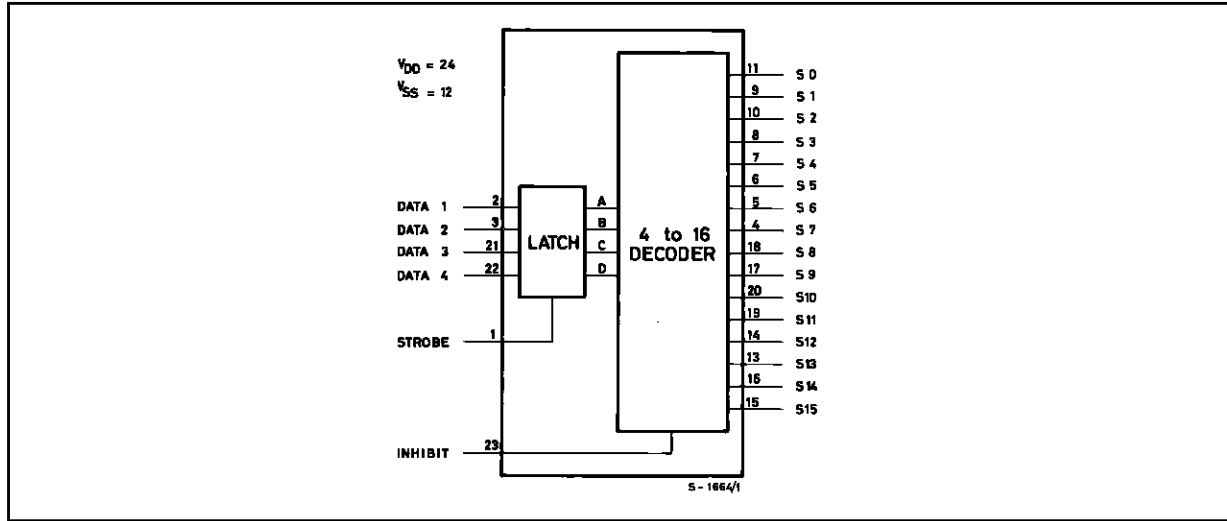




# HCC/HCF4514B/4515B

## FUNCTIONAL DIAGRAM



## ABSOLUTE MAXIMUM RATINGS

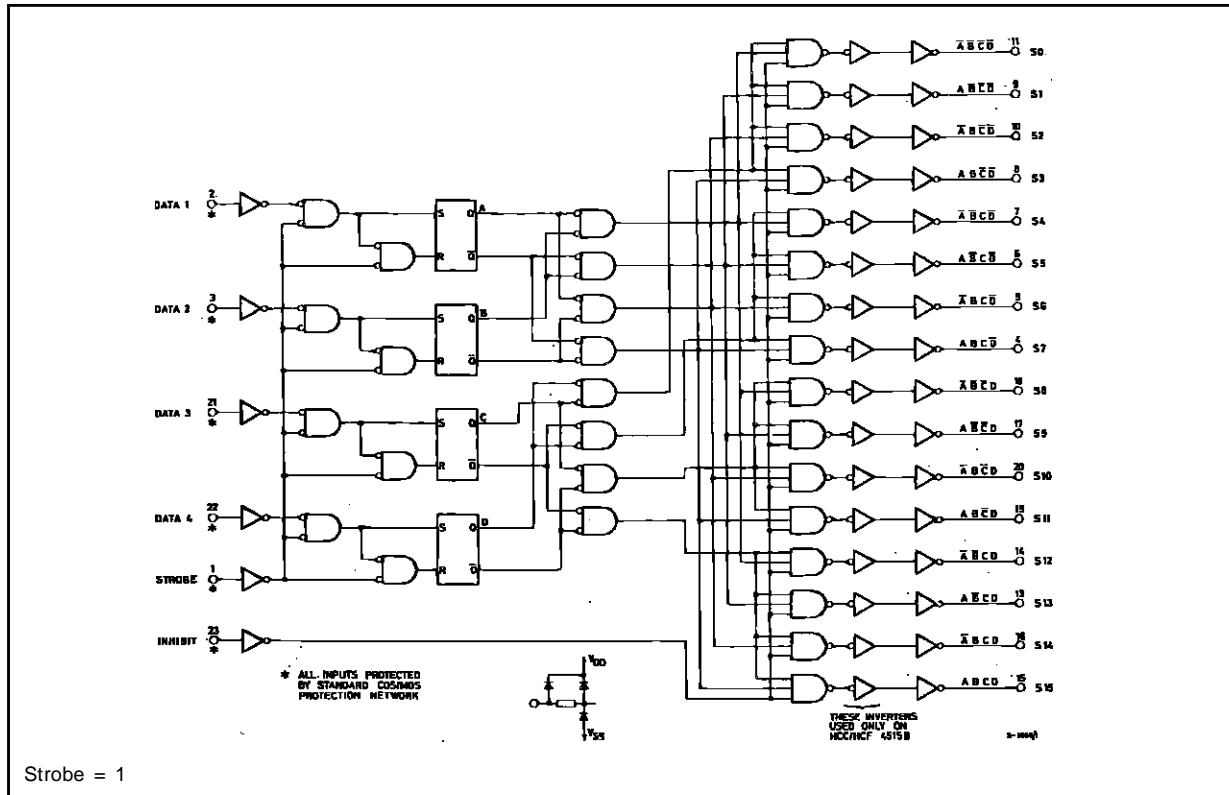
Symbol	Parameter	Value	Unit
V <sub>DD</sub> *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V
V <sub>i</sub>	Input Voltage	- 0.5 to V <sub>DD</sub> + 0.5	V
I <sub>I</sub>	DC Input Current (any one input)	± 10	mA
P <sub>tot</sub>	Total Power Dissipation (per package) Dissipation per Output Transistor for T <sub>op</sub> = Full Package-temperature Range	200 100	mW
T <sub>op</sub>	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V <sub>DD</sub>	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V
V <sub>I</sub>	Input Voltage	0 to V <sub>DD</sub>	V
T <sub>op</sub>	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C

LOGIC DIAGRAM AND TRUTH TABLE

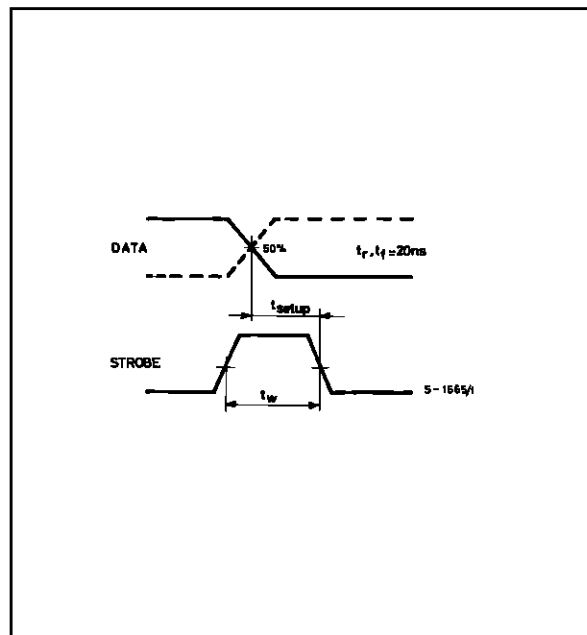


Inhibit	Data Inputs				Selected Output HCC/HCF 4514B = Logic 1 (High) HCC/HCF 4515B = Logic 0 (Low)
	D	C	B	A	
0	0	0	0	0	S0
0	0	0	0	1	S1
0	0	0	1	0	S2
0	0	0	1	1	S3
0	0	1	0	0	S4
0	0	1	0	1	S5
0	0	1	1	0	S6
0	0	1	1	1	S7
0	1	0	0	0	S8
0	1	0	0	1	S9
0	1	0	1	0	S10
0	1	0	1	1	S11
0	1	1	0	0	S12
0	1	1	0	1	S13
0	1	1	1	0	S14
0	1	1	1	1	S15
1	X	X	X	X	All Outputs = 0, HCC/HCF 4514B All Outputs = 1, HCC/HCF 4515B

X = Don't Care  
1 = high

WAVEFORMS

Setup Time and Strobe Pulse Width.



# HCC/HCF4514B/4515B

## STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V <sub>I</sub> (V)	V <sub>O</sub> (V)	I <sub>O</sub>   ( $\mu$ A)	V <sub>DD</sub> (V)	T <sub>Low</sub> *		25°C			T <sub>High</sub> *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I <sub>L</sub>	Quiescent Current	HCC Types	0/ 5			5		5		0.04	5		150	$\mu$ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
		0/20			20		100		0.08	100		3000		
		HCF Types	0/ 5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
0/15				15		80		0.04	80		600			
V <sub>OH</sub>	Output High Voltage	0/ 5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V <sub>OL</sub>	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V <sub>IH</sub>	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V <sub>IL</sub>	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I <sub>OH</sub>	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA	
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
		0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4			
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
0/10	9.5			10	- 1.3		- 1.1	- 2.6		- 0.9				
0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4					
I <sub>OL</sub>	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I <sub>IH</sub> , I <sub>IL</sub>	Input Leakage Current	HCC Types	0/18	Any Input		18		$\pm$ 0.1		$\pm$ 10 <sup>-5</sup>	$\pm$ 0.1		$\pm$ 1	
		HCF Types	0/15	Any Input		15		$\pm$ 0.3		$\pm$ 10 <sup>-5</sup>	$\pm$ 0.3		$\pm$ 1	
C <sub>I</sub>	Input Capacitance		Any Input						5	7.5			pF	

\* T<sub>Low</sub>= - 55°C for HCC device : - 40°C for HCF device.

\* T<sub>High</sub>= + 125°C for HCC device : + 85°C for HCF device.

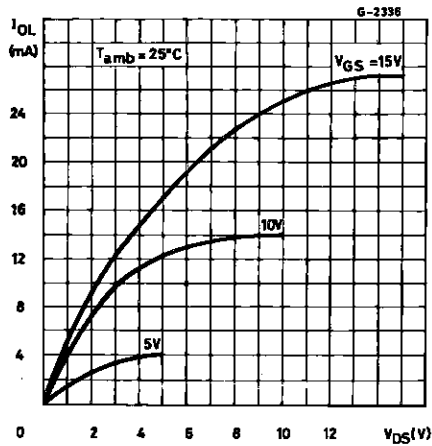
The Noise Margin for both "1" and "0" level is : 1V min. with V<sub>DD</sub> = 5V, 2V min. with V<sub>DD</sub> = 10V, 2.5 V min. with V<sub>DD</sub> = 15V.

**DYNAMIC ELECTRICAL CHARACTERISTICS**

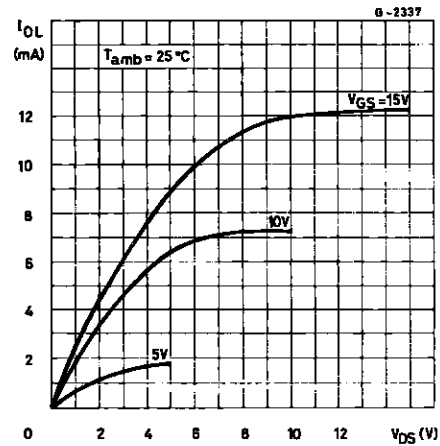
( $T_{amb} = 25^{\circ}\text{C}$ ,  $C_L = 50\text{pF}$ ,  $R_L = 200\text{k}\Omega$ , all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			$V_{DD}$ (V)	Min.	Typ.	Max.	
$t_{PHL}$ , $t_{PLH}$	Propagation Delay Time	Strobe or Data	5		485	970	ns
			10		185	370	
			15		135	270	
		Inhibit	5		250	500	ns
			10		110	220	
			15		85	170	
$t_{THL}$ , $t_{TFL}$	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
$t_w$	Strobe Pulse Width		5	250	125		ns
			10	100	50		
			15	75	40		
$t_{setup}$	Setup Time		5	150	75		ns
			10	70	35		
			15	40	20		

Typical Output Low (sink) Current Characteristics.

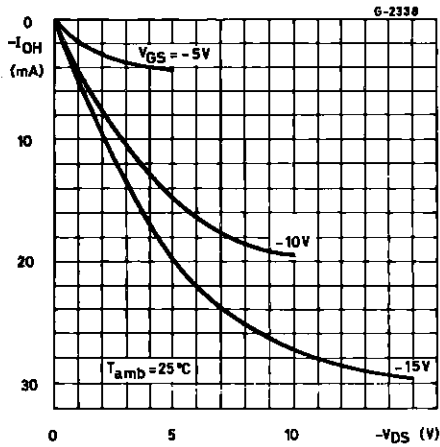


Minimum Output Low (sink) Current Characteristics.

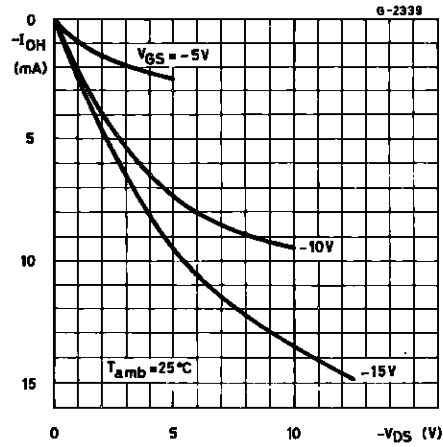


# HCC/HCF4514B/4515B

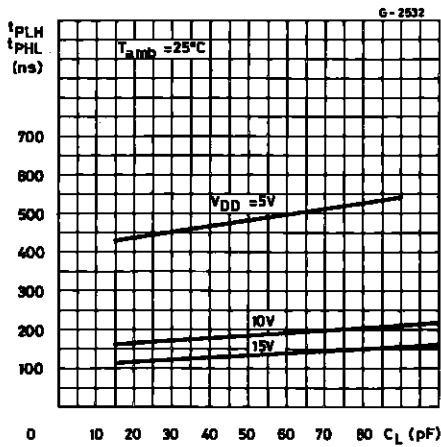
Typical Output High (source) Current Characteristics.



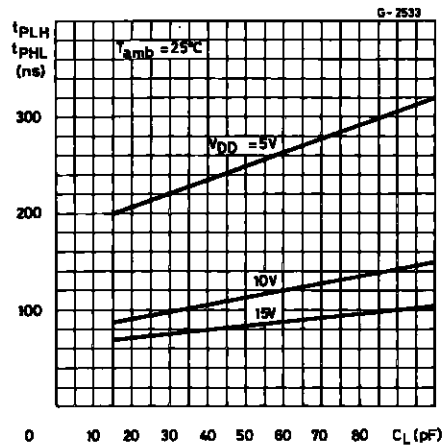
Minimum Output High (source) Current Characteristics.



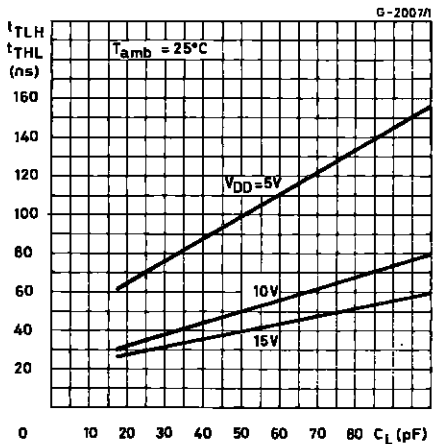
Typical Strobe or Data Propagation Delay Time vs. Load Capacitance.



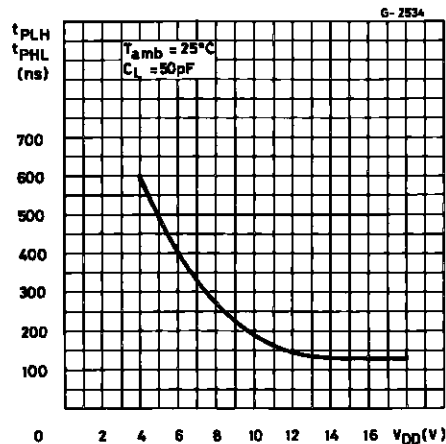
Typical Inhibit Propagation Delay Time vs. Load Capacitance.



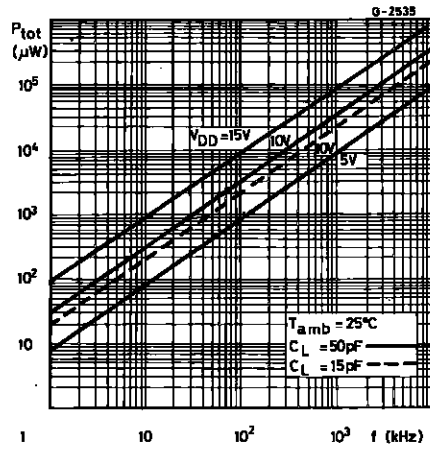
Typical Transition Time vs. Load Capacitance.



Typical Strobe or Data Propagation Delay Time vs. Supply Voltage.

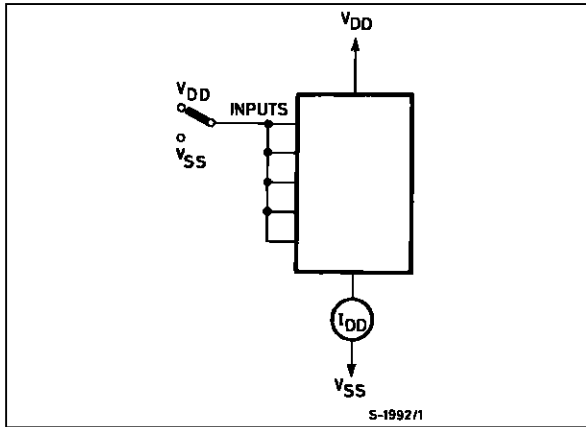


Typical Power Dissipation vs. Frequency.

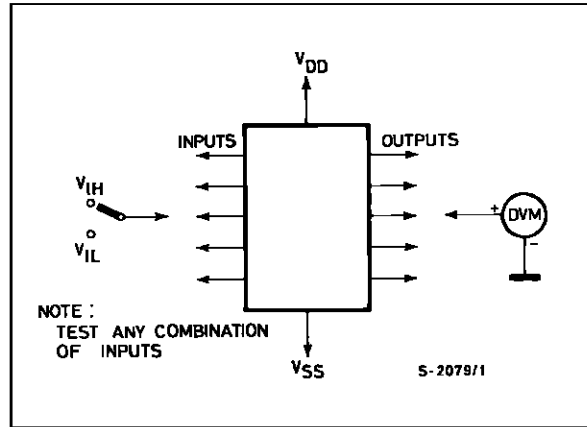


TEST CIRCUITS

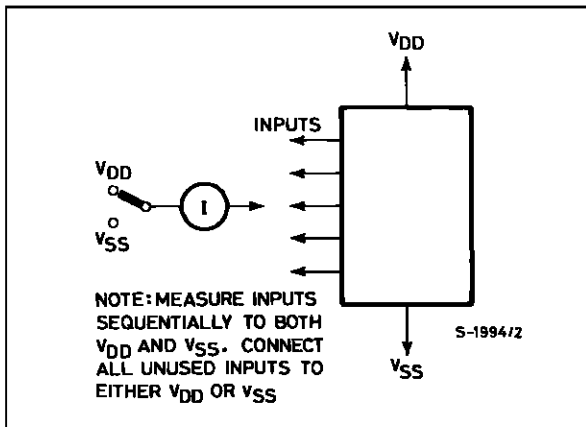
Quiescent Device Current.



Noise Immunity.

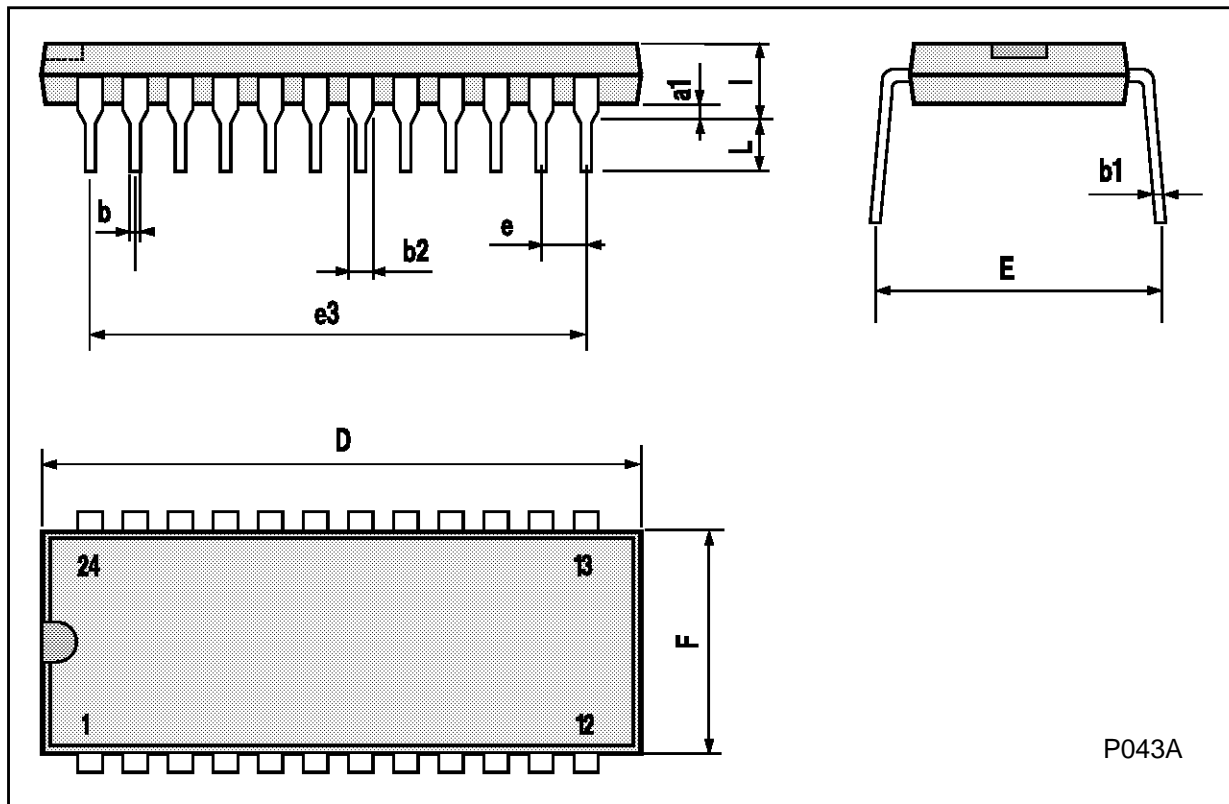


Input Leakage Current.



**Plastic DIP24 (0.25) MECHANICAL DATA**

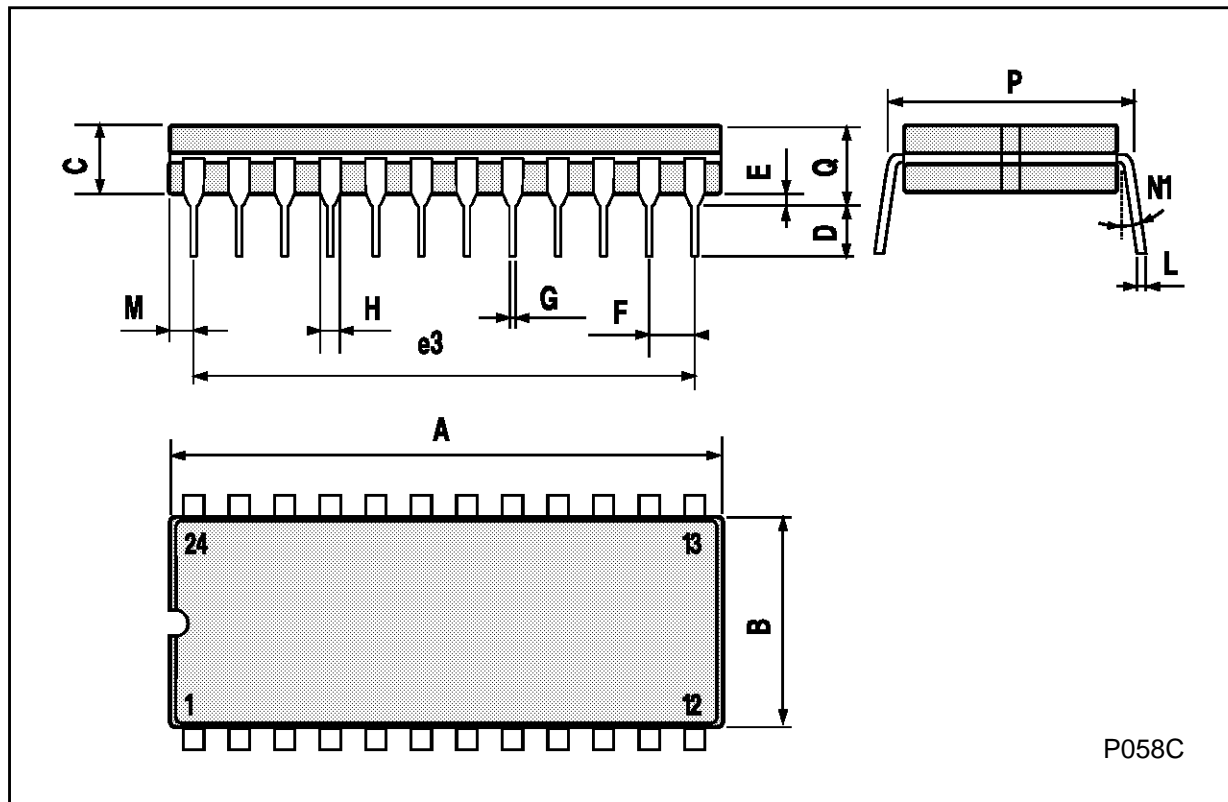
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1		0.63			0.025	
b		0.45			0.018	
b1	0.23		0.31	0.009		0.012
b2		1.27			0.050	
D			32.2			1.268
E	15.2		16.68	0.598		0.657
e		2.54			0.100	
e3		27.94			1.100	
F			14.1			0.555
l		4.445			0.175	
L		3.3			0.130	





## Ceramic DIP24 MECHANICAL DATA

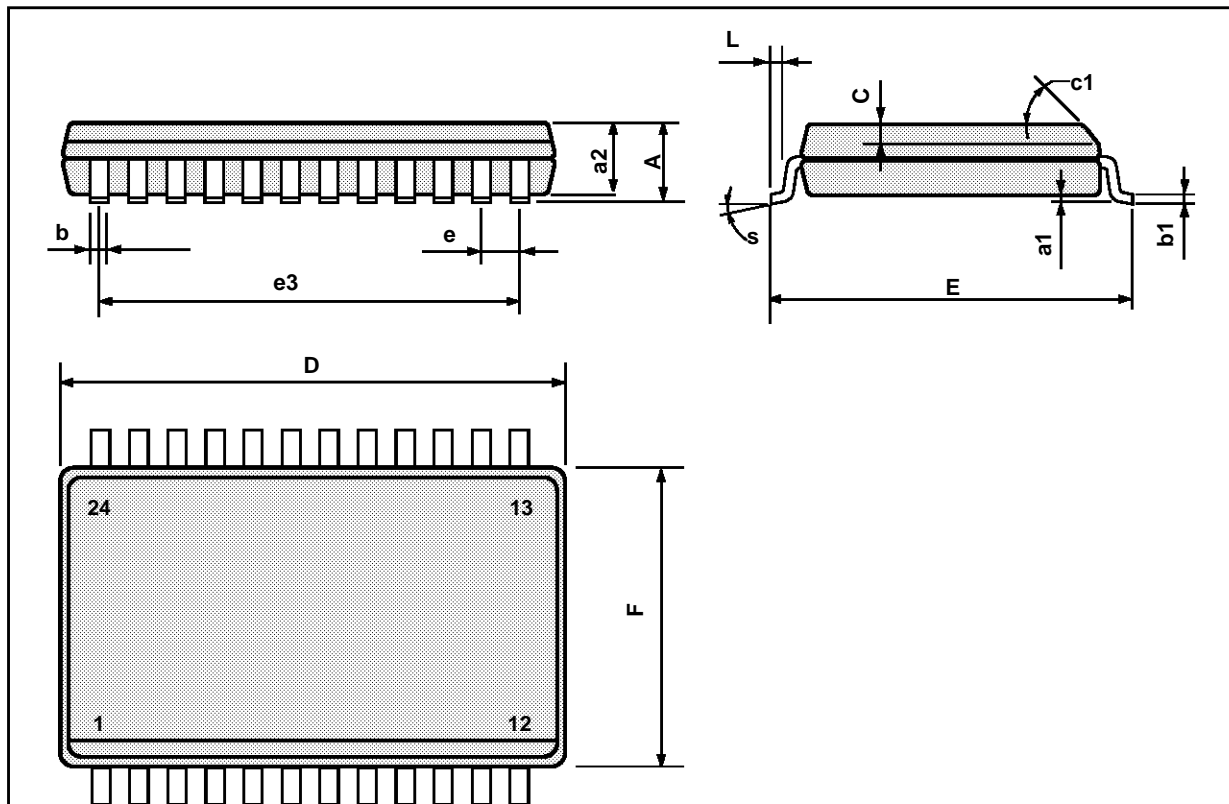
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			32.3			1.272
B	13.05		13.36	0.514		0.526
C	3.9		5.08	0.154		0.200
D	3			0.118		
E	0.5		1.78	0.020		0.070
e3		27.94			1.100	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
I	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	1.52		2.49	0.060		0.098
N1	4° (min.), 15° (max.)					
P	15.4		15.8	0.606		0.622
Q			5.71			0.225



P058C

**SO24 MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			2.65			0.104
a1	0.10		0.20	0.004		0.007
a2			2.45			0.096
b	0.35		0.49	0.013		0.019
b1	0.23		0.32	0.009		0.012
C		0.50			0.020	
c1	45° (typ.)					
D	15.20		15.60	0.598		0.614
E	10.00		10.65	0.393		0.420
e		1.27			0.05	
e3		13.97			0.55	
F	7.40		7.60	0.291		0.299
L	0.50		1.27	0.19		0.050
S	8° (max.)					



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